



**CHENMKO ENTERPRISE CO.,LTD**

*Halogens free devices*

**SURFACE MOUNT  
NPN Digital Silicon Transistor**

VOLTAGE 50 Volts CURRENT 100 mAmpere

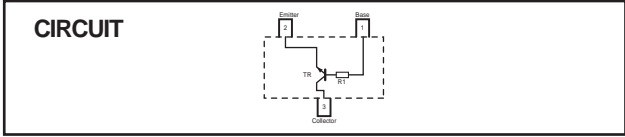
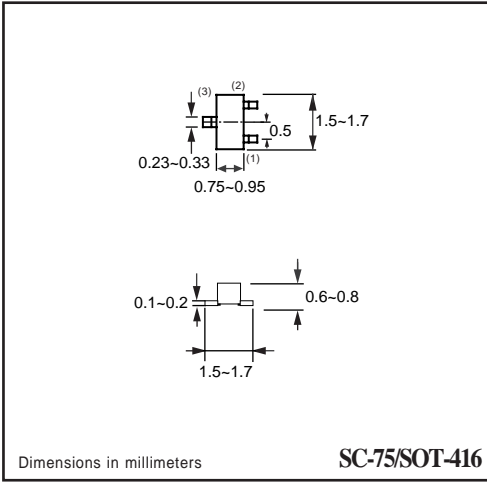
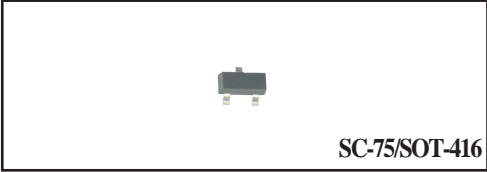
**CHDTC115TEGP**

**APPLICATION**  
\* Switching circuit, Inverter, Interface circuit, Driver circuit.

**FEATURE**  
\* Small surface mounting type. (SC-75/SOT-416)  
\* High current gain.  
\* Suitable for high packing density.  
\* Low collector-emitter saturation.  
\* High saturation current capability.  
\* Internal isolated NPN transistors in one package.  
\* Built in single resistor(R1=100kΩ, Typ. )

**CONSTRUCTION**  
\* One NPN transistors and bias of thin-film resistors in one package.

**MARKING**  
TEE



**LIMITING VALUES**  
In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base voltage		50	V
V <sub>CEO</sub>	Collector-Emitter voltage		50	V
V <sub>EBO</sub>	Emitter-Base voltage		5	V
I <sub>C(Max.)</sub>	Collector current		100	mA
P <sub>D</sub>	Power dissipation	T <sub>amb</sub> ≤ 25 °C, Note 1	150	mW
T <sub>STG</sub>	Storage temperature		-55 +150	°C
T <sub>J</sub>	Junction temperature		-55 +150	°C
R <sub>θJ-S</sub>	Thermal resistance , Note 1	junction - soldering point	140	°C/W

**Note**  
1. Transistor mounted on an FR4 printed-circuit board.

## RATING CHARACTERISTIC ( CHDTC115TEGP )

### CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
BVCBO	Collector-base breakdown voltage	$I_C=50\mu\text{A}$	50	–	–	V
BVCEO	Collector-emitter breakdown voltage	$I_C=1.0\text{mA}$	50	–	–	V
BVEBO	Emitter-base breakdown voltage	$I_E=50\mu\text{A}$	5.0	–	–	V
ICBO	Collector cutoff current	$V_{CB}=50\text{V}$	–	–	0.5	$\mu\text{A}$
IEBO	Emitter cutoff current	$V_{EB}=4\text{V}$	–	–	0.5	$\mu\text{A}$
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C/I_B=1\text{mA}/0.1\text{mA}$	–	–	0.3	V
$h_{FE}$	DC current gain	$I_C=1\text{mA}; V_{CE}=5.0\text{V}$	100	250	600	
$R_1$	Input resistor		70	100	130	$\text{K}\Omega$
$f_T$	Transition frequency	$I_C=5\text{mA}, V_{CE}=10.0\text{V}$ $f=100\text{MHz}$	–	250	–	MHz

### Note

1. Pulse test:  $t_p \leq 300\mu\text{s}; \delta \leq 0.02$ .

## RATING CHARACTERISTIC CURVES ( CHDTC115TEGP )

### Typical Electrical Characteristics

Fig.1 DC current gain vs. collector current

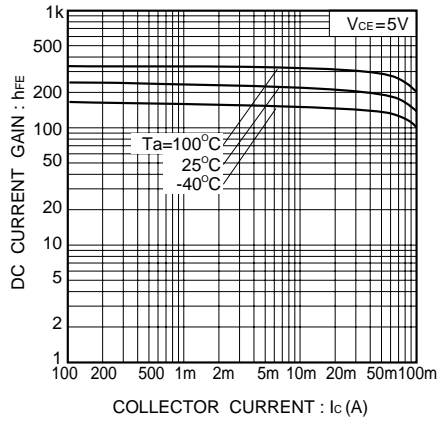


Fig.2 Collector-emitter voltage vs. collector current

